

TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM8G45, SM8J45, SM8G45A, SM8J45A

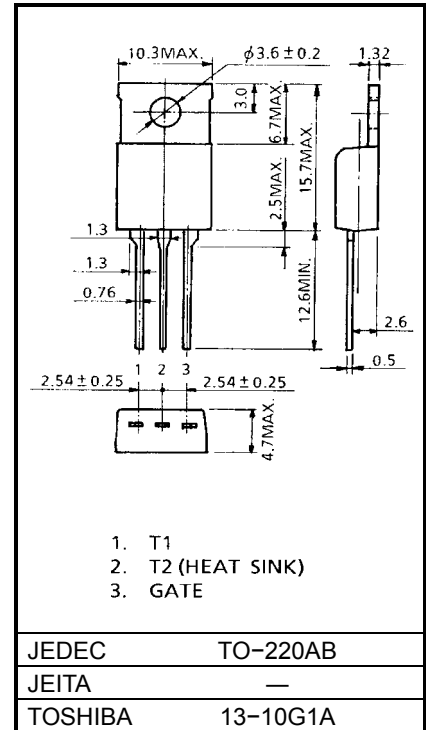
AC POWER CONTROL APPLICATIONS

- Repetitive Peak Off-State Voltage : $V_{DRM} = 400, 600V$
- R.M.S ON-State Current : $I_T (RMS) = 8A$
- High Commutating (dv / dt)

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage	SM8G45 SM8G45A	400	V
	SM8J45 SM8J45A	600	
R.M.S On-State Current (Full Sine Waveform $T_c = 105^\circ C$)	$I_T (RMS)$	8	A
Peak One Cycle Surge On-State Current (Non-Repetitive)	I_{TSM}	80 (50Hz)	A
		88 (60Hz)	
$I^2 t$ Limit Value	$I^2 t$	32	$A^2 s$
Critical Rate of Rise of On-State Current	di / dt	50	$A / \mu s$
Peak Gate Power Dissipation	P_{GM}	5	W
Average Gate Power Dissipation	$P_G (AV)$	0.5	W
Peak Gate Voltage	V_{GM}	10	V
Peak Gate Current	I_{GM}	2	A
Junction Temperature	T_j	-40~125	$^\circ C$
Storage Temperature Range	T_{stg}	-40~125	$^\circ C$

Unit: mm

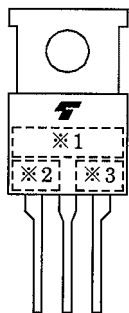


Weight: 2.0g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

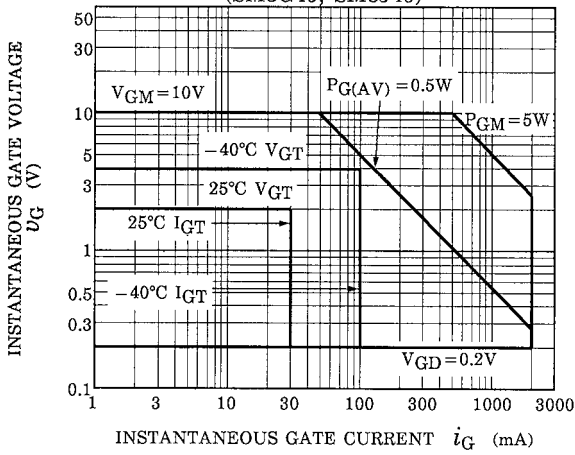
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT	
Repetitive Peak Off-State Current		I_{DRM}	$V_{DRM} = \text{Rated}, T_j = 125^\circ\text{C}$	—	—	2	mA	
Gate Trigger Voltage	SM8G45 SM8J45	I	$V_D = 12\text{V}$ $R_L = 20\Omega$	T2 (+), Gate (+)	—	—	2	V
		II		T2 (+), Gate (-)	—	—	2	
		III		T2 (-), Gate (-)	—	—	2	
		IV		T2 (-), Gate (+)	—	—	—	
	SM8G45A SM8J45A	I		T2 (+), Gate (+)	—	—	1.5	
		II		T2 (+), Gate (-)	—	—	1.5	
		III		T2 (-), Gate (-)	—	—	1.5	
		IV		T2 (-), Gate (+)	—	—	—	
Gate Trigger Current	SM8G45 SM8J45	I	$V_D = 12\text{V}$ $R_L = 20\Omega$	T2 (+), Gate (+)	—	—	30	mA
		II		T2 (+), Gate (-)	—	—	30	
		III		T2 (-), Gate (-)	—	—	30	
		IV		T2 (-), Gate (+)	—	—	—	
	SM8G45A SM8J45A	I		T2 (+), Gate (+)	—	—	20	
		II		T2 (+), Gate (-)	—	—	20	
		III		T2 (-), Gate (-)	—	—	20	
		IV		T2 (-), Gate (+)	—	—	—	
Peak On-State Voltage		V_{TM}	$I_{TM} = 12\text{A}$	—	—	1.5	V	
Gate Non-Trigger Voltage		V_{GD}	$V_D = \text{Rated}, T_c = 125^\circ\text{C}$	0.2	—	—	V	
Holding Current		I_H	$V_D = 12\text{V}, I_{TM} = 1\text{A}$	—	—	50	mA	
Thermal Resistance		$R_{th(j-c)}$	Junction to Case, AC	—	—	2.0	$^\circ\text{C} / \text{W}$	
Critical Rate of Rise of Off-State Voltage at Commutation	SM8G45 SM8J45	$(dv / dt)_c$	$V_{DRM} = 400\text{V},$ $(di / dt)_c = -4.5\text{A} / \text{ms}$ $T_j = 125^\circ\text{C}$	10	—	—	V / μs	
	SM8G45A SM8J45A			4	—	—		

MARKING

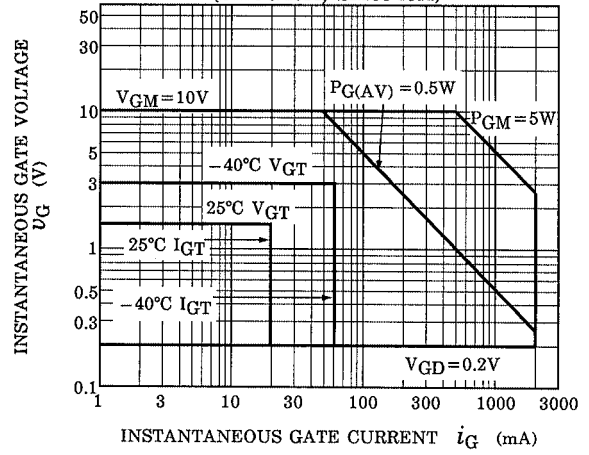


NUMBER	SYMBOL		MARK
* 1	TYPE	SM8G45, SM8G45A	M8G45
		SM8J45, SM8J45A	M8J45
* 2		SM8G45A, SM8J45A	A
* 3	Lot Number 		Example 8A : January 1998 8B : February 1998 8L : December 1998

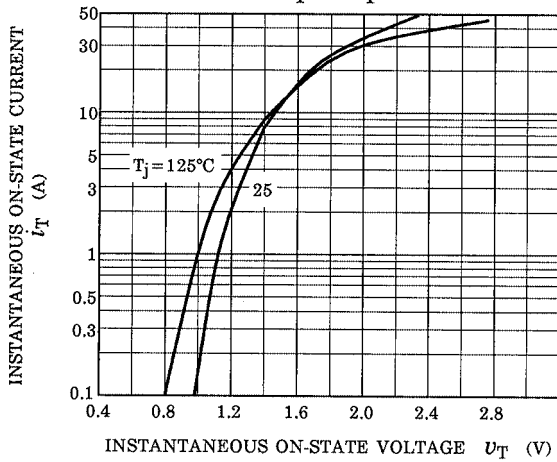
GATE TRIGGER CHARACTERISTIC
(SM8G45, SM8J45)



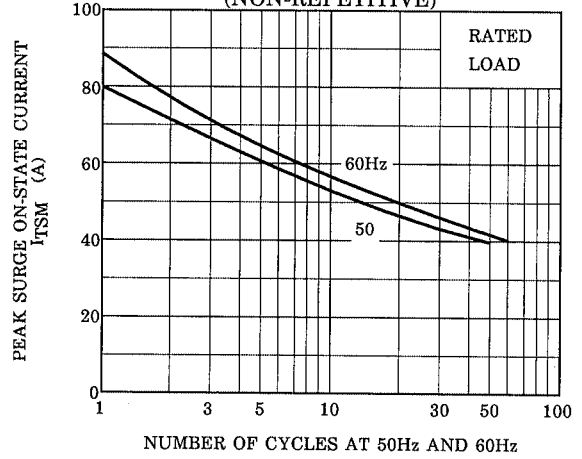
GATE TRIGGER CHARACTERISTIC
(SM8G45A, SM8J45A)



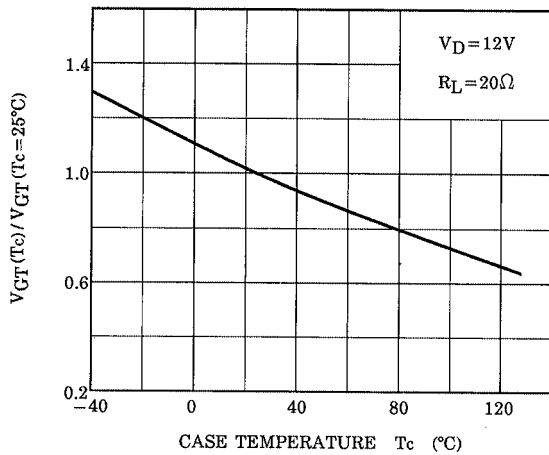
$i_T - v_T$



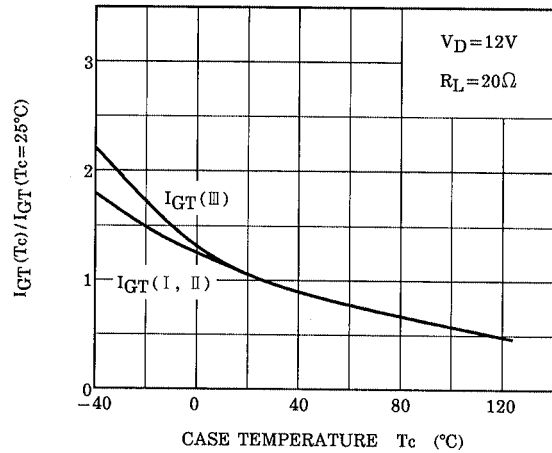
SURGE ON-STATE CURRENT
(NON-REPETITIVE)

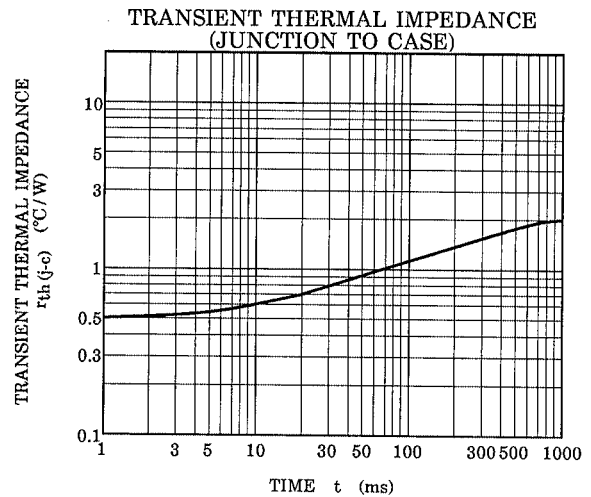
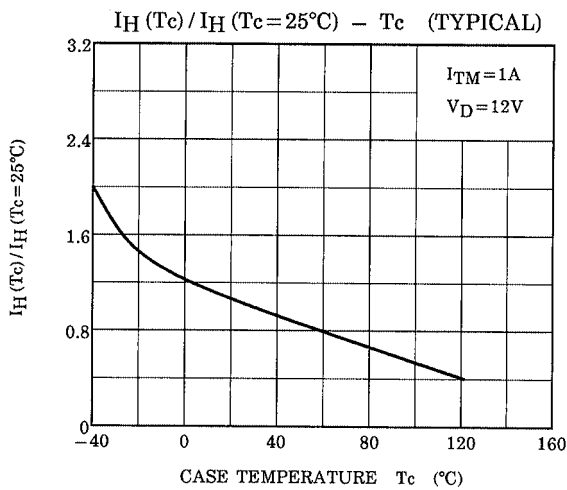
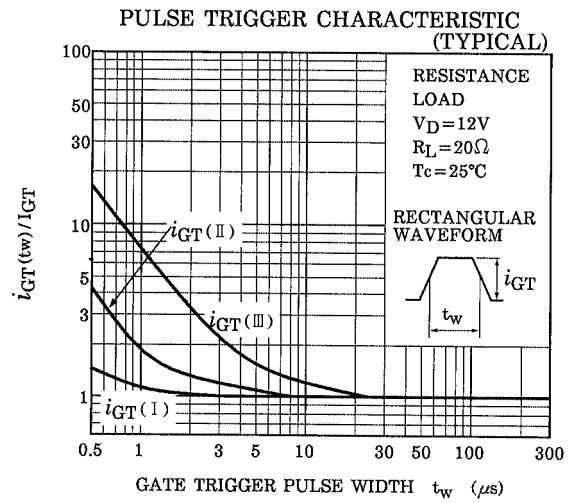
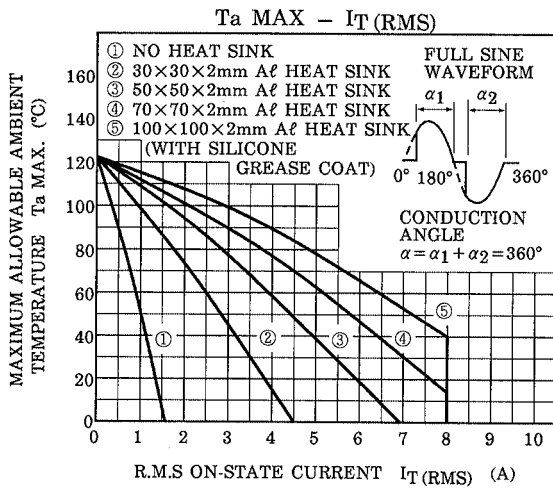
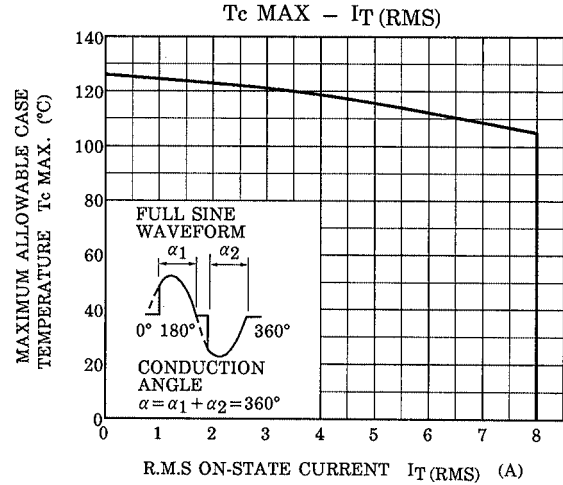
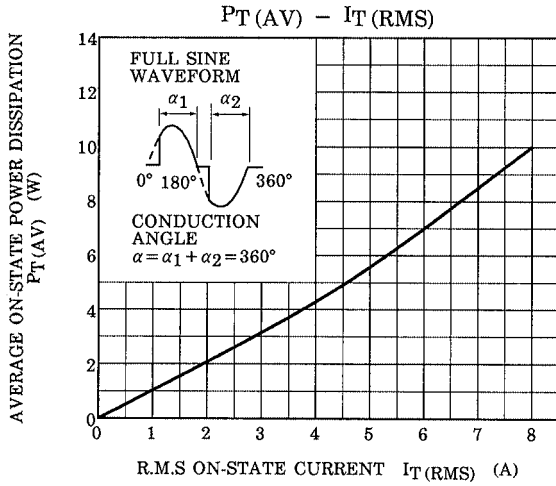


$V_{GT}(T_c) / V_{GT}(T_c=25^\circ\text{C}) - T_c$ (TYPICAL)



$I_{GT}(T_c) / I_{GT}(T_c=25^\circ\text{C}) - T_c$ (TYPICAL)





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